

S/N 09/259,762

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Zhiping Yin et al.

Examiner: Jose Diaz

Serial No.: 09/259,762

Group Art Unit: 2815

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Title: OXYGEN PLASMA TREATMENT FOR NITRIDE SURFACE TO REDUCE
PHOTO FOOTING

PATENT

#3/A
12-7-00

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

CEM
11-28



Applicant has reviewed the Office Action mailed on August 28, 2000. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please cancel claims 4 and 12-20 and amend claim 1 as follows:

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1. A method for reducing profile distortion in semiconductor fabrication, comprising:
- providing a semiconductor substrate comprising a film comprising silicon-nitride;
 - treating the film in a vacuum of about 3.0-6.5 Torr, for a time of about 10 seconds to about 5 minutes, and in an atmosphere comprising oxygen plasma wherein the oxygen plasma flow rate is at least about 300 sccm oxygen thereby rendering the substrate resistant to profile distortion to make a treated substrate;
 - applying a resist to the treated substrate; and
 - patterning the resist.

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